JJT10N65SC

650V 10A Trench and Field Stop IGBT

Key performance:

- V_{CE}=650V
- I_C=10A@T_C=100℃
- $V_{CE(sat)}$=1.80 V

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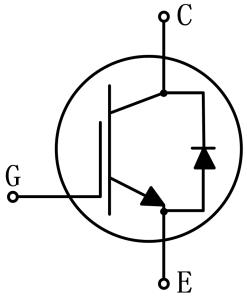
Features:

- High ruggedness performance
- 10μs short circuit capability
- Positive $V_{CE\ (sat)}$ temperature coefficient
- High efficiency for motor control
- Excellent current sharing in parallel operation
- RoHS compliant



Applications:

- Home appliances
- Motor drives

Package parameters

Type	Marking	Package	Packaging method
JJT10N65SC	T1065SC	TO-263	Tape and reel

Maximum ratings

Symbol	Parameter	Values	Unit
V_{CES}	Collector-emitter voltage	650	V
V_{GES}	Gate-emitter voltage	±30	V
I_C	Continuous collector current (T_C=25℃)	20	A
	Continuous collector current (T_C=100℃)	10	A
I_{CM}	Pulsed collector current, t_p limited by Tj_{max}	40	A
I_F	Diode continuous forward current (T_C=100℃)	10	A
I_{FM}	Diode maximum current, t_p limited by Tj_{max}	40	A
t_{sc}	Short circuit withstand time	10	μs
P_{tot}	Power dissipation (T_C=25℃)	30	W
	Power dissipation (T_C=100℃)	12	W
Tj	Operating junction temperature range	-40 to +150	℃
T_{stg}	Storage temperature range	-55 to +150	℃

Thermal characteristics

Symbol	Parameter	Values		Unit
		Typ.	Max.	
$R_{th(j-c)}$	Thermal resistance, junction to case for IGBT	-	1.5	K/ W
$R_{th(j-c)}$	Thermal resistance, junction to case for Diode	-	1.8	K/ W
$R_{th(j-a)}$	Thermal resistance, junction to ambient	-	50	K/ W

Electrical characteristics of IGBT (*Tj*=25℃ unless otherwise specified)

Static characteristics

Symbol	Parameter	Test condition	Values			Unit
			Min.	Typ.	Max.	
BV_{CES}	Collector-emitter breakdown voltage	V_{GE}=0V, I_C=250μA	650	-	-	V
I_{CES}	Collector-emitter leakage current	V_{CE}=650V, V_{GE}=0V	-	-	100	μA
I_{GES}	Gate leakage current, forward	V_{GE}=20V, V_{CE}=0V	-	-	250	nA
	Gate leakage current, reverse	V_{GE}=-20V, V_{CE}=0V	-	-	-250	nA
$V_{GE(th)}$	Gate-emitter threshold voltage	V_{GE}=V_{CE}, I_C=250μA	5.5	5.7	6.0	V
$V_{CE(sat)}$	Collector-emitter saturation voltage	V_{GE}=15V, I_C=10A	-	1.8	-	V

Dynamic characteristics

Symbol	Parameter	Test condition	Values			Unit
			Min.	Typ.	Max.	
C_{ies}	Input capacitance	V_{CE}=30V V_{GE}=0V f=1MHz	-	670	-	pF
C_{oes}	Output capacitance		-	37	-	pF
C_{res}	Reverse transfer capacitance		-	10	-	pF
Q_g	Total gate charge	V_{CC}=520V V_{GE}=15V I_C=10A	-	28	-	nC

Switching characteristics

Symbol	Parameter	Test condition	Values			Unit
			Min.	Typ.	Max.	
$t_{d(on)}$	Turn-on delay time	V_{CC}=400V V_{GE}=0/15V I_C=10A R_G=10Ω Inductive load	-	12	-	ns
t_r	Rise time		-	11	-	ns
$t_{d(off)}$	Turn-off delay time		-	71	-	ns
t_f	Fall time		-	74	-	ns
E_{on}	Turn-on energy		-	0.18	-	mJ
E_{off}	Turn-off energy		-	0.17	-	mJ

Symbol	Parameter	Test condition	Values			Unit
			Min.	Typ.	Max.	
$t_{d(on)}$	Turn-on delay time	V_{CC}=400V V_{GE}=0/15V I_C=10A R_G=10Ω Inductive load Tj=150℃	-	10	-	ns
t_r	Rise time		-	12	-	ns
$t_{d(off)}$	Turn-off delay time		-	86	-	ns
t_f	Fall time		-	112	-	ns
E_{on}	Turn-on energy		-	0.21	-	mJ
E_{off}	Turn-off energy		-	0.25	-	mJ

Diode Characteristics (Tj=25℃ unless otherwise specified)

Symbol	Parameter	Test condition	Values			Unit
			Min.	Typ.	Max.	
V_F	Diode forward voltage	I_F=10A	-	1.4	-	V
		I_F=10A, Tj=150℃	-	1.2	-	V
t_{rr}	Diode reverse recovery time	V_R=400V I_F=10A di_F/dt=-750A/μs	-	57	-	ns
I_{rrm}	Diode peak reverse recovery current		-	12	-	A
Q_{rr}	Diode reverse recovery charge		-	411	-	nC
t_{rr}	Diode reverse recovery time	V_R=400V I_F=10A di_F/dt=-750A/μs Tj=150℃	-	118	-	ns
I_{rrm}	Diode peak reverse recovery current		-	13	-	A
Q_{rr}	Diode reverse recovery charge		-	728	-	nC

Typical performance characteristics

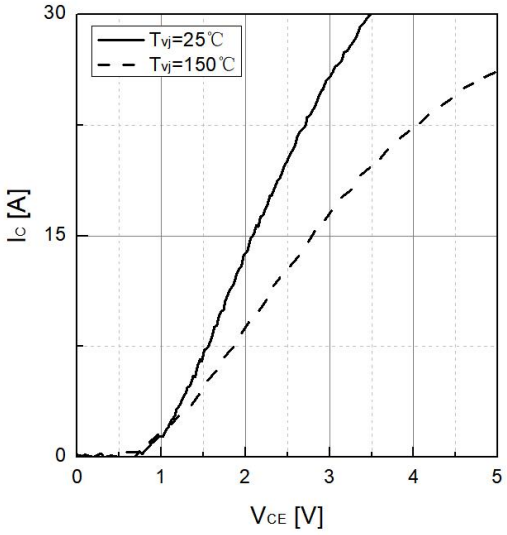


Fig 1. Typical output characteristic (T_{vj}=25℃)

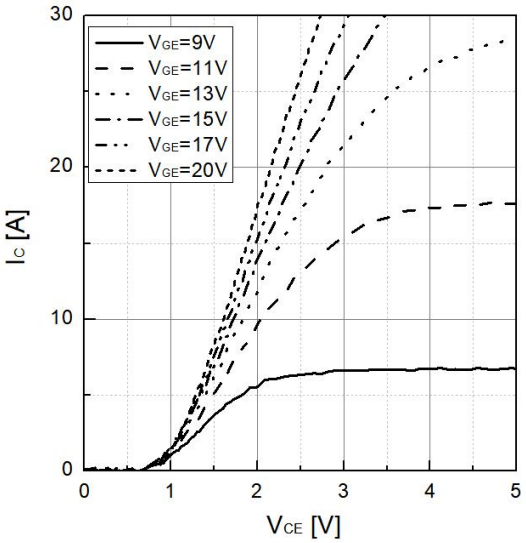


Fig 2. Typical output characteristic (T_{vj}=25℃)

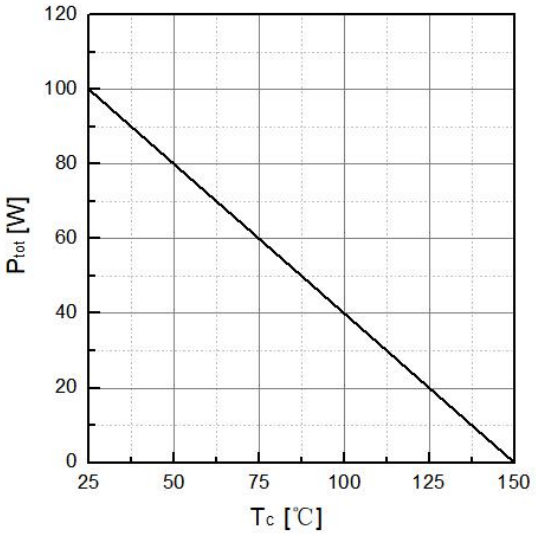


Fig 3. Power dissipation as a function of T_C

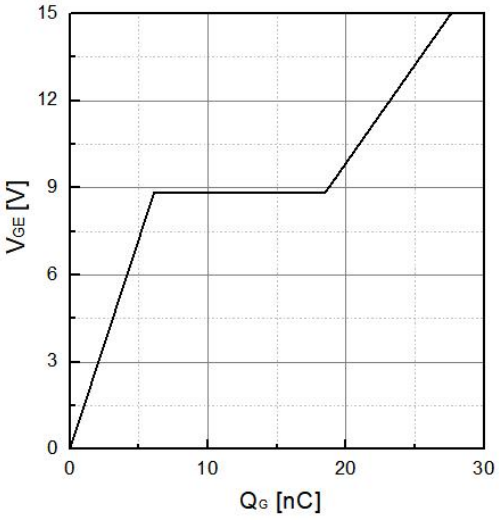


Fig 4. Typical Gate charge

Typical performance characteristics

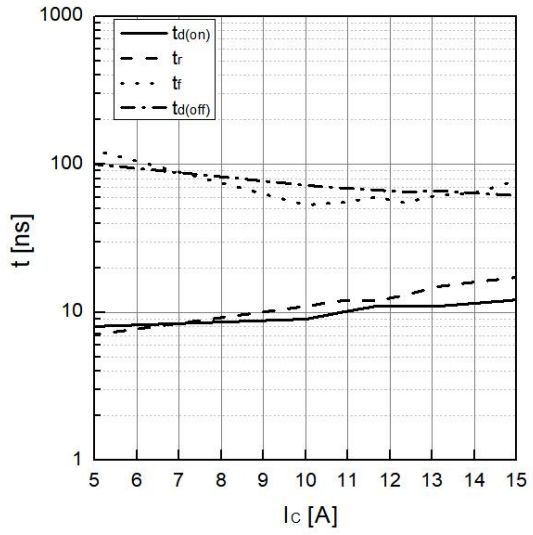


Fig 5. Typical switching time as a function of I_C

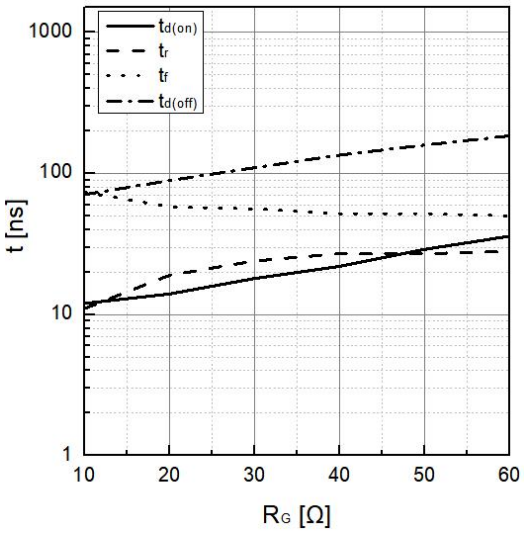


Fig 6. Typical switching times as a function of R_G

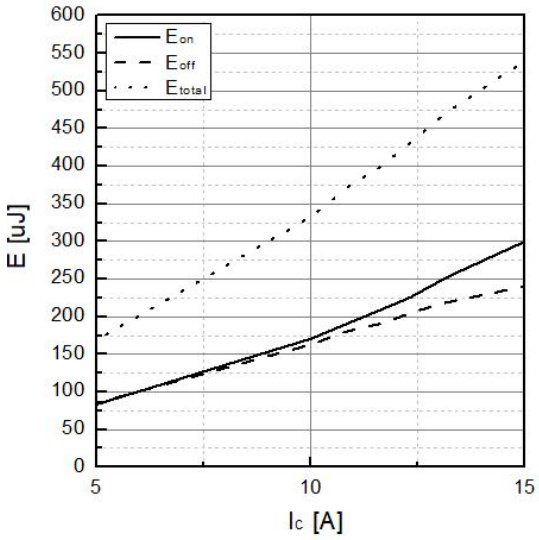


Fig 7. Typical switching energy losses as a function of I_C

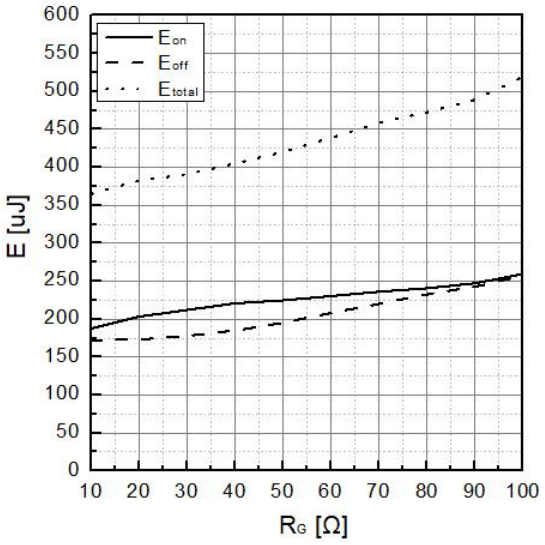


Fig 8. Typical switching energy losses as a function of R_G

Typical performance characteristics

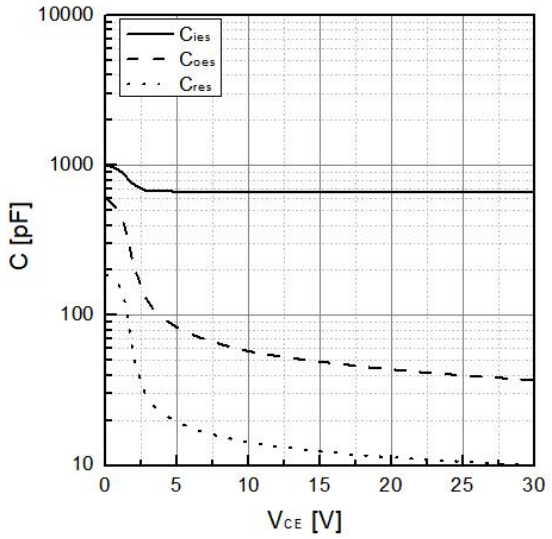


Fig 9. Typical capacitance as a function of V_C(f=1Mhz, V_{GE}=0V)

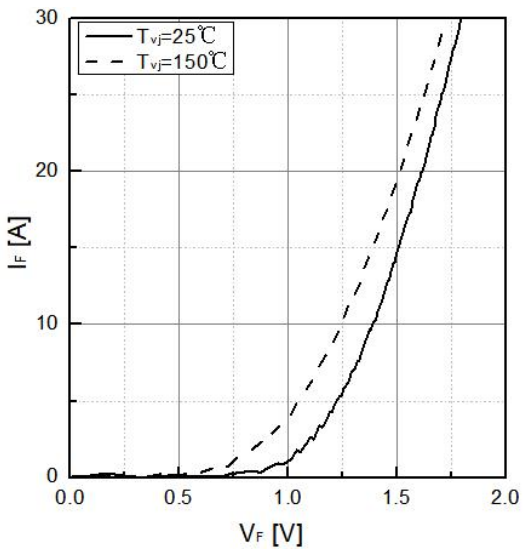


Fig 10. Typical I_F as a function of V_F

Package dimension

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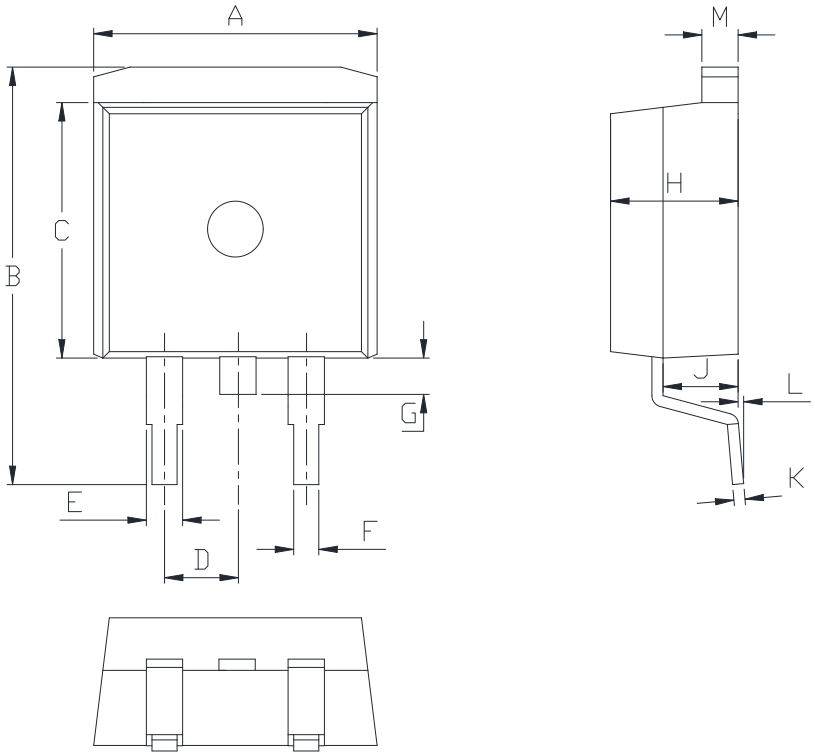

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.90	-	10.20	0.390	-	0.402
B	14.70	-	15.80	0.579	-	0.622
C	9.4	-	9.6	0.37	-	0.378
D	-	2.54	-	-	0.100	-
E	1.20	-	1.40	0.047	-	0.055
F	0.75	-	0.85	0.029	-	0.033
G	-	-	1.75	-	-	0.069
H	4.40	-	4.70	0.173	-	0.185
J	2.30	-	2.70	0.091	-	0.106
K	0.38	-	0.55	0.015	-	0.022
L	0	0.10	0.25	0	0.004	0.010
M	1.25	-	1.35	0.049	-	0.053

Revision history

Date	Revision	Changes
2023-12-23	Rev 1.0	Release of the datasheet

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